

High Speed Infrared Emitting Diodes, 890 nm, GaAlAs, DH

VSMF2890RGX01



VSMF2890GX01



DESCRIPTION

VSMF2890RG(G)X01 series are infrared, 890 nm emitting diodes in GaAlAs (DH) technology with high radiant power and high speed, molded in clear, untinted plastic packages (with lens) for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 2.3 x 2.3 x 2.8
- AEC-Q101 qualified
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Terminal configurations: gullwing or reserve gullwing
- Package matches with detector VEMD2000X01 series
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

AUTOMOTIVE GRADE



RoHS COMPLIANT
GREEN [5-2008]**

APPLICATIONS

- IrDA compatible data transmission
- 3D TV
- Miniature light barrier
- Photointerrupters
- Optical switch
- Shaft encoders
- IR emitter source for proximity applications

PRODUCT SUMMARY				
COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMF2890RGX01	40	± 12	890	30
VSMF2890GX01	40	± 12	890	30

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMF2890RGX01	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Reverse gullwing
VSMF2890GX01	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Gullwing

Note

- MOQ: minimum order quantity

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

VSMF2890RGX01, VSMF2890GX01



Vishay Semiconductors High Speed Infrared Emitting Diodes,
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ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100\text{ }\mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100\text{ }\mu\text{s}$	I_{FSM}	1	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^{\circ}\text{C}$
Soldering temperature	Acc. figure 9, J-STD-020	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	250	K/W

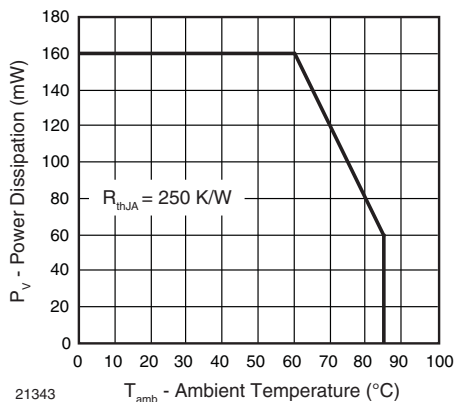


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

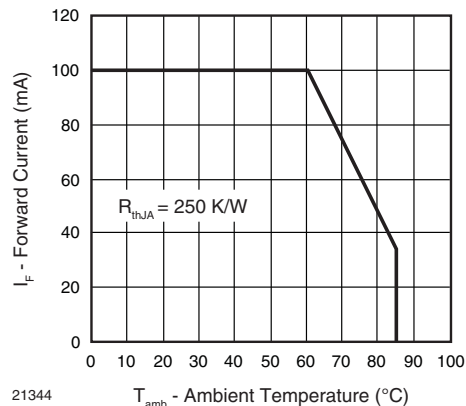


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F	1.25	1.4	1.6	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.3		V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}		- 1.8		mV/K
	$I_F = 100\text{ mA}$	TK_{V_F}		- 1.1		mV/K
Reverse current	$V_R = 5\text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$	C_J		125		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	20	40	60	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e		350		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		40		mW
Temperature coefficient of ϕ_e	$I_F = 100\text{ mA}$	TK_{ϕ_e}		- 0.35		%/K
Angle of half intensity		ϕ		± 12		deg
Peak wavelength	$I_F = 30\text{ mA}$	λ_p	870	890	910	nm
Spectral bandwidth	$I_F = 30\text{ mA}$	$\Delta\lambda$		40		nm
Temperature coefficient of λ_p	$I_F = 30\text{ mA}$	TK_{λ_p}		0.25		nm/K
Rise time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_r		30		ns
Fall time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_f		30		ns
Cut-off frequency	$I_{DC} = 70\text{ mA}$, $I_{AC} = 30\text{ mA pp}$	f_c		12		MHz
Virtual source diameter		d		1.5		mm



VSMF2890RGX01, VSMF2890GX01

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BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

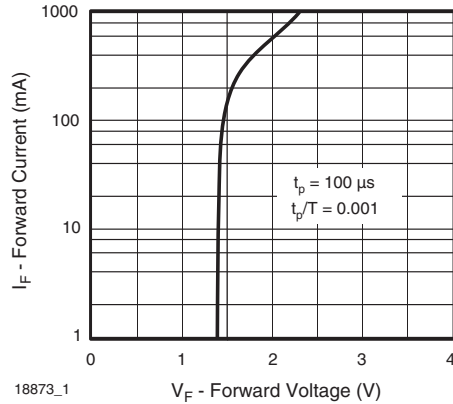


Fig. 3 - Forward Current vs. Forward Voltage

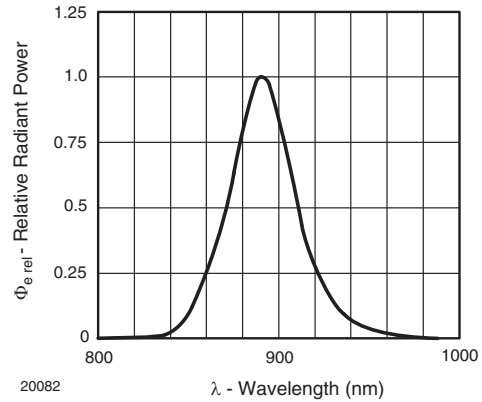


Fig. 6 - Relative Radiant Power vs. Wavelength

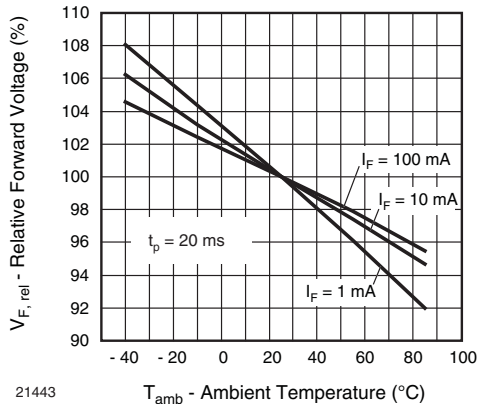


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

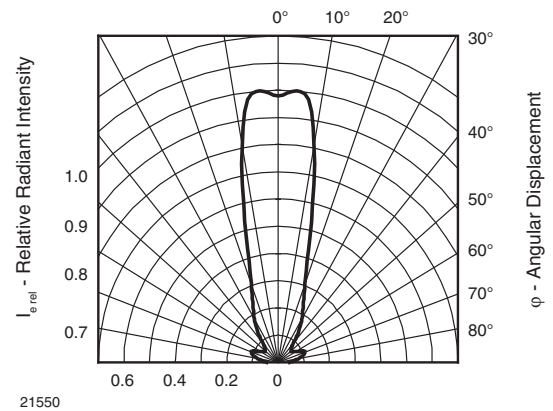


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

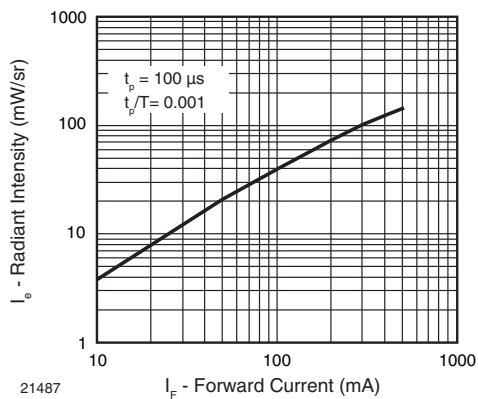


Fig. 5 - Radiant Intensity vs. Forward Current

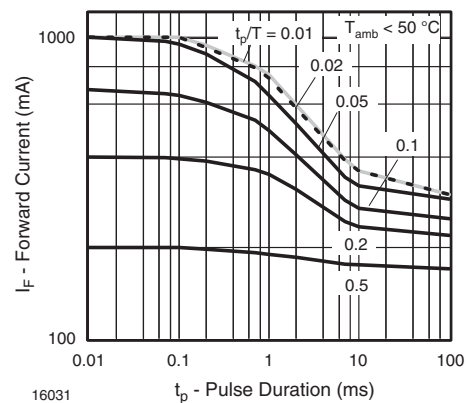


Fig. 8 - Pulse Forward Current vs. Pulse Duration

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SOLDER PROFILE

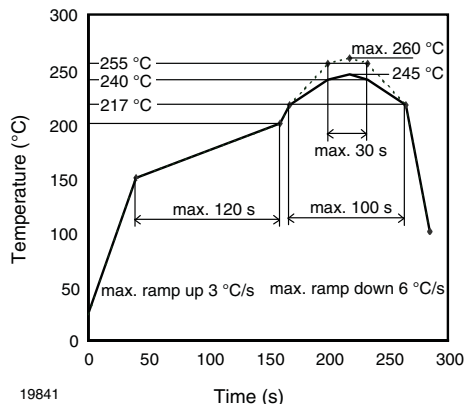


Fig. 9 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

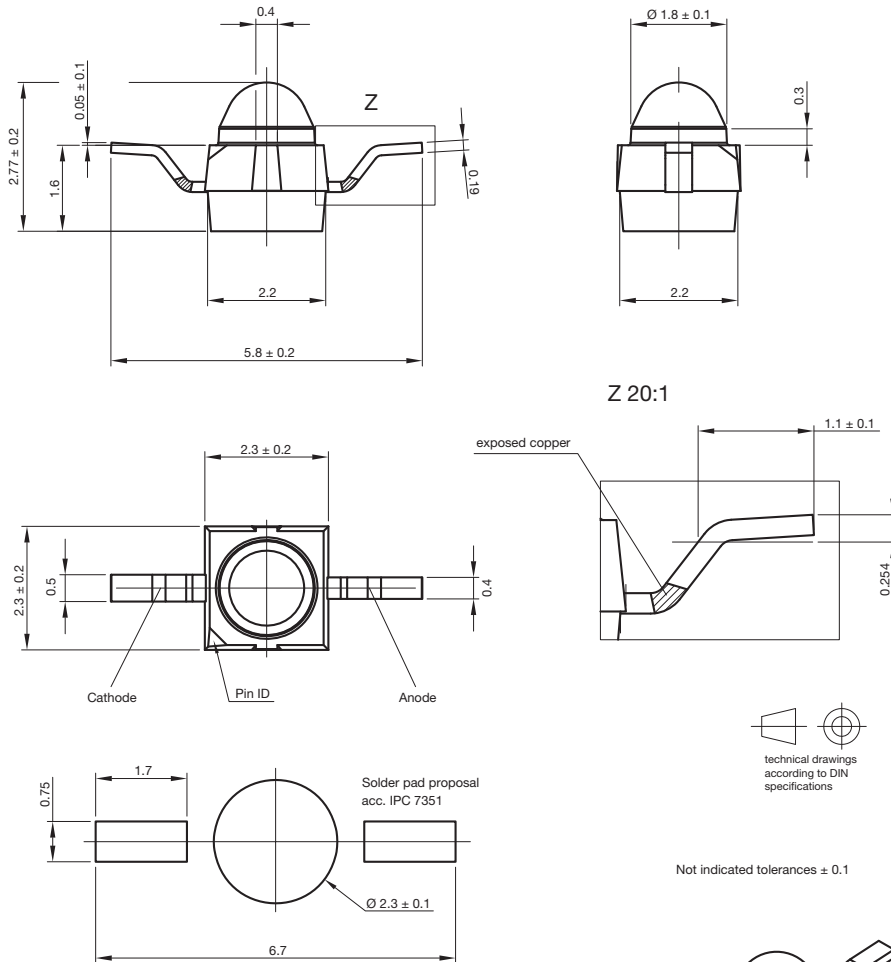
Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020.

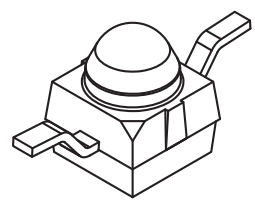
DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.

PACKAGE DIMENSIONS in millimeters: VSMF2890RGX01



Drawing-No.: 6.544-5391.02-4
Issue: 2; 18.03.10
21517

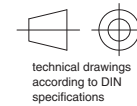
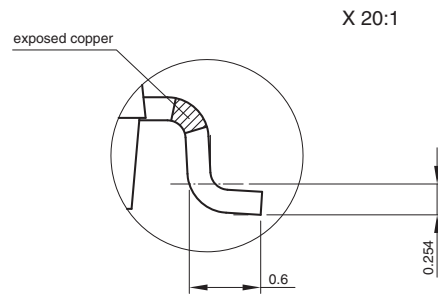
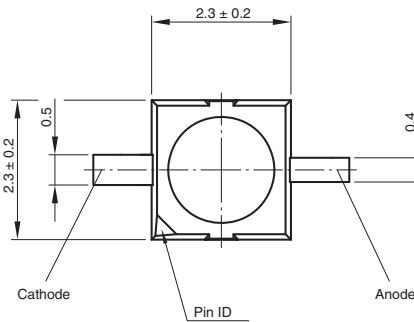
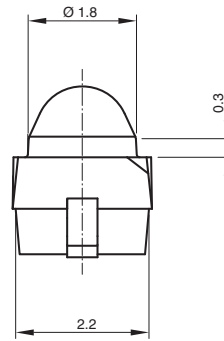
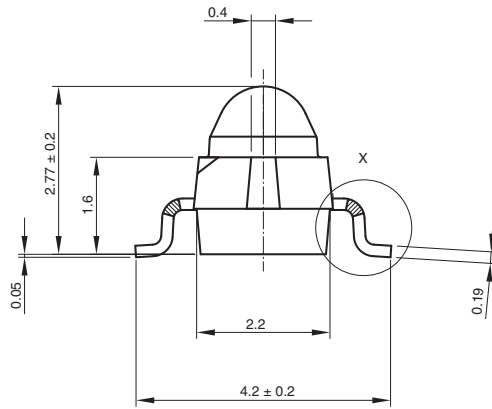




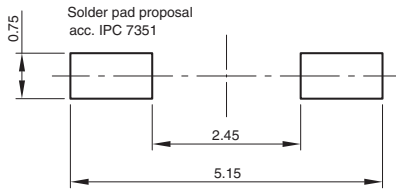
VSMF2890RGX01, VSMF2890GX01

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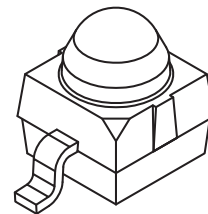
PACKAGE DIMENSIONS in millimeters: VSMF2890GX01



technical drawings according to DIN specifications



Not indicated tolerances ± 0.1



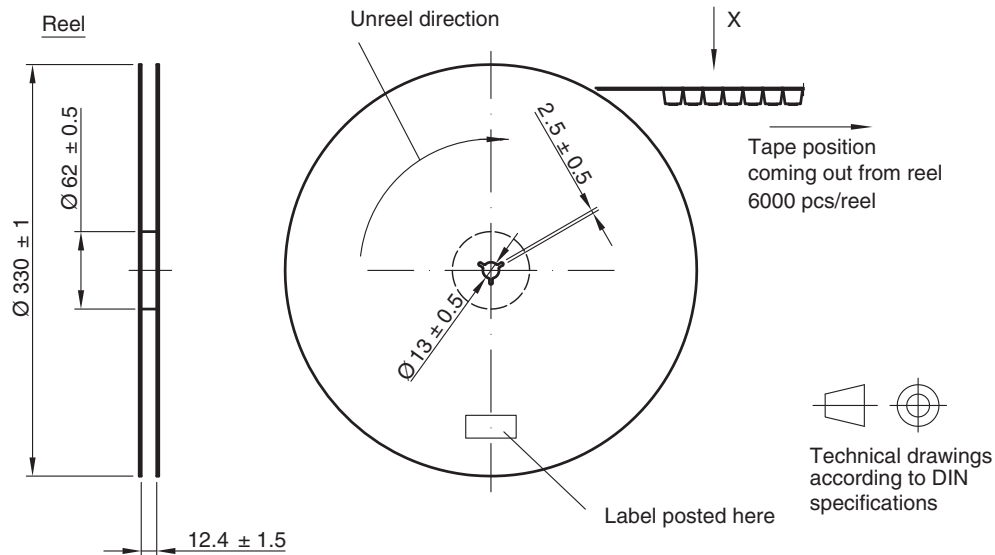
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Issue: 4; 18.03.10
21488

VSMF2890RGX01, VSMF2890GX01

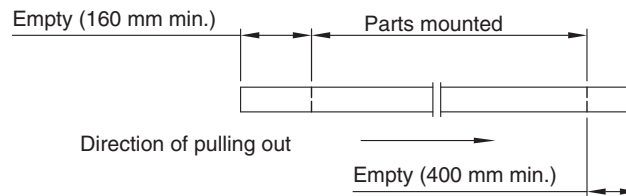


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TAPING AND REEL DIMENSIONS in millimeters: VSMF2890RGX01

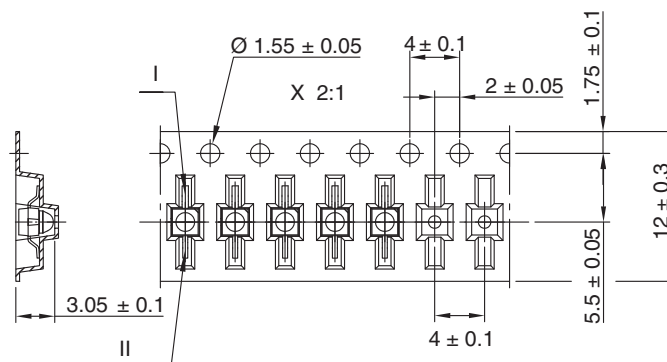


Leader and trailer tape:



Terminal position in tape

Device	Lead I	Lead II
VEMT2000	Collector	Emitter
VEMT2500		
VEMD2000	Cathode	Anode
VEMD2500		
VSMB2000		
VSMG2000	Anode	Cathode
VSMY2850RG		



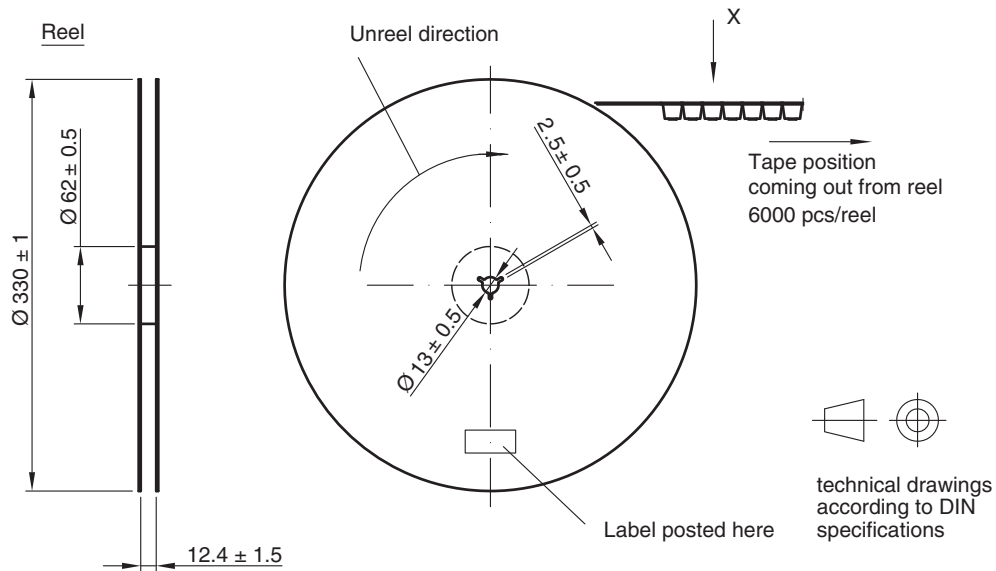
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Issue: 2; 18.03.10
21572



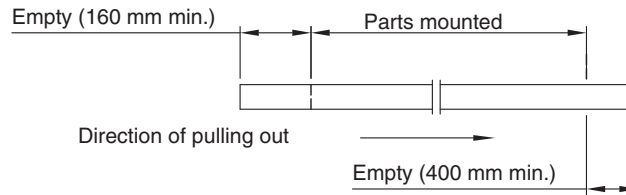
VSMF2890RGX01, VSMF2890GX01

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TAPING AND REEL DIMENSIONS in millimeters: VSMF2890GX01

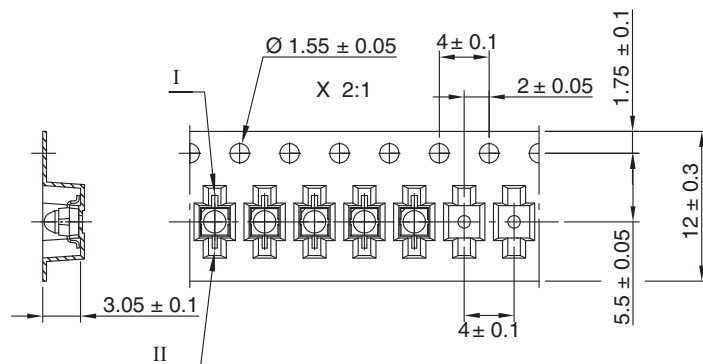


Leader and trailer tape:



Terminal position in tape

Device	Lead I	Lead II
VEMT2020	Collector	Emitter
VEMT2520		
VSMB2020	Cathode	Anode
VSMG2020		
VEMD2020		
VEMD2520		
VSMY2850G	Anode	Cathode



Drawing-No.: 9.800-5091.01-4

Issue: 3; 18.03.10

21571



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